

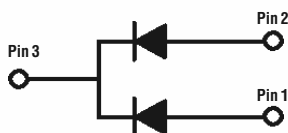


Data Sheet

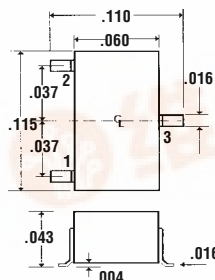
200 mW EPITAXIAL PLANAR DIODES

FMBBAV70

Description



Mechanical Dimensions



Features

- PLANAR PROCESS
- 200 mW POWER DISSIPATION

- INDUSTRY STANDARD SOT-23 PACKAGE
- MEETS UL SPECIFICATION 94V-0

Electrical Characteristics @ 25°C.	FMBBAV70	Units
Maximum Ratings	FMBBAV70	
Peak Reverse Voltage... V_{RM}	85	Volts
RMS Reverse Voltage... $V_{R(rms)}$	75	Volts
Average Forward Rectified Current... I_O	625	mAmps
Non-Repetitive Peak Forward Surge Current... I_{FSM}	4.0	Amps
Forward Voltage... V_F @ $I_F = 100$ mA	1.0	Volts
DC Reverse Current... I_R @ $V_R = 70V$	0.1	μAmps
Power Dissipation... P_D	200	mW
Typical Junction Capacitance... C_j	1.5	pF
Reverse Recovery Time... t_{RR}	4.0	nS
Operating Temperature Range... T_J	-25 to 85	°C
Storage Temperature Range... T_{STRG}	-65 to 150	°C

Device Under Test

